Fig. 1

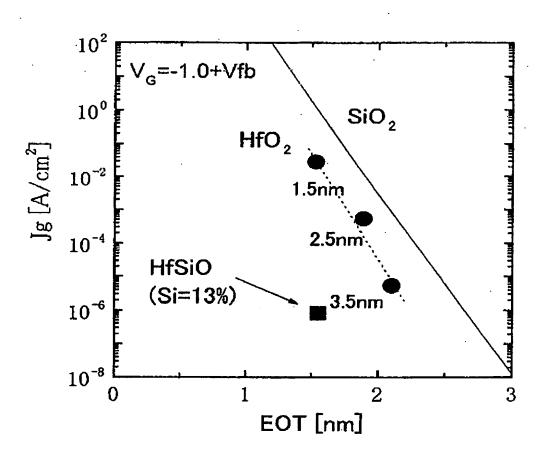


Fig. 2

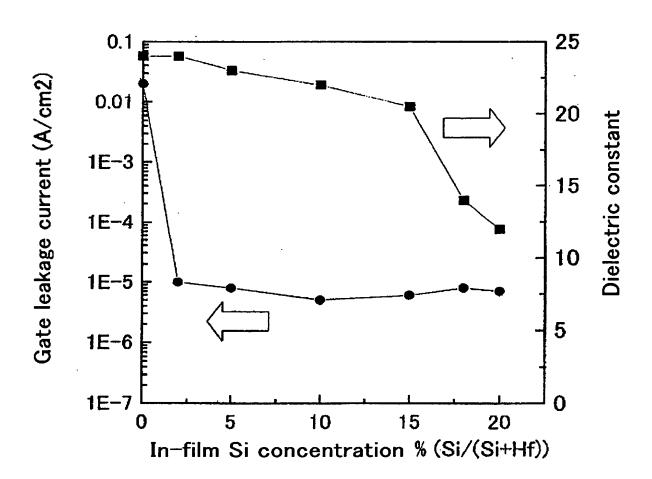


Fig. 3

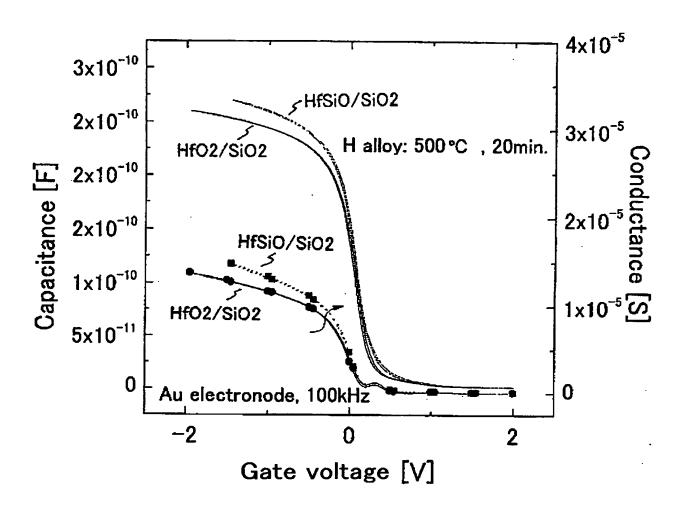


Fig. 4

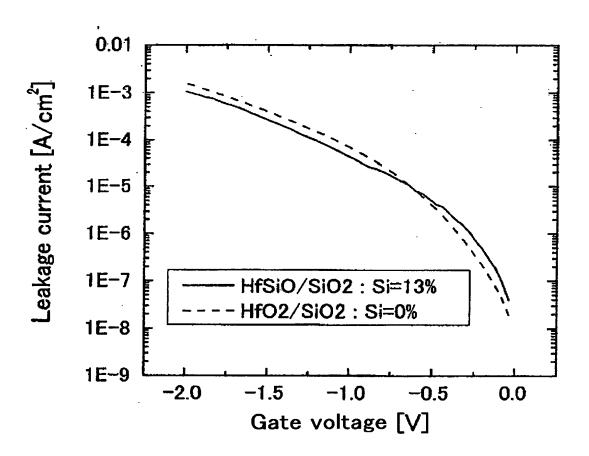
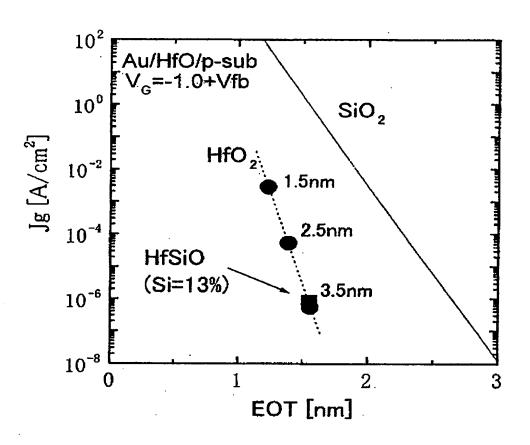


Fig. 5



BEST AVAILABLE COPY

Title: SEMICONDUCTOR DEVICE HAVING A MIS-TYPE FET, AND METHODS FOR MANUFACTURING THE SAME AND FORMING A METAL OXIDE FILM Inventor(s): Toru TATSUMI, et al. Appl. No.: Unassigned

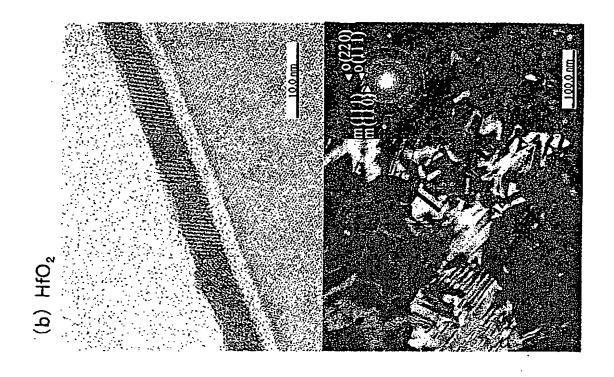
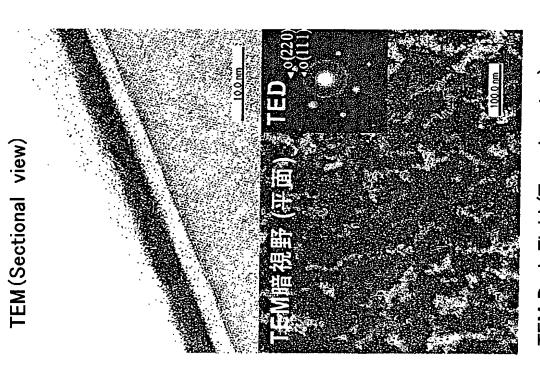


Fig. 6

(a) HfSiO



TEM Dark Field (Top plan view)

Fig. 7

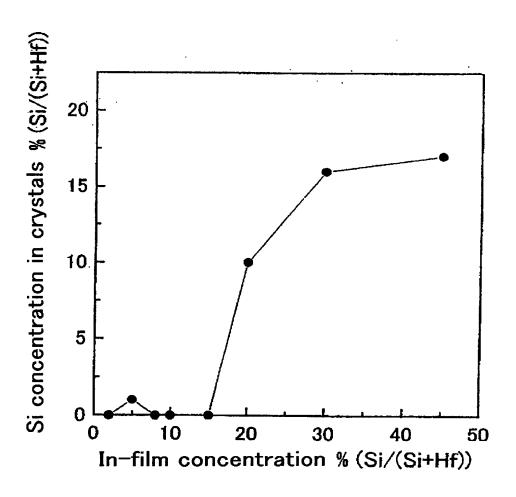
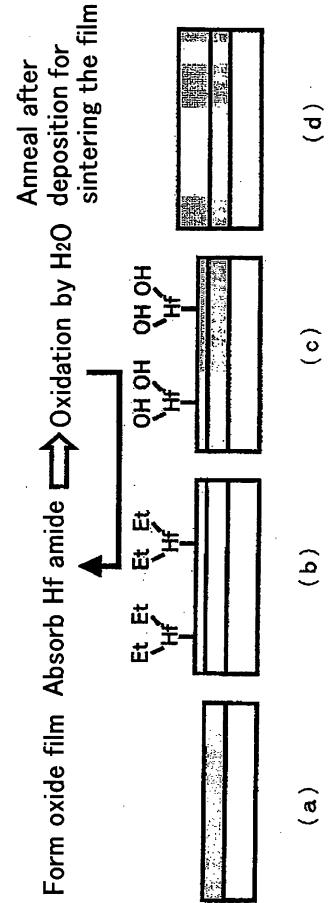
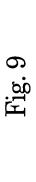


Fig. 8





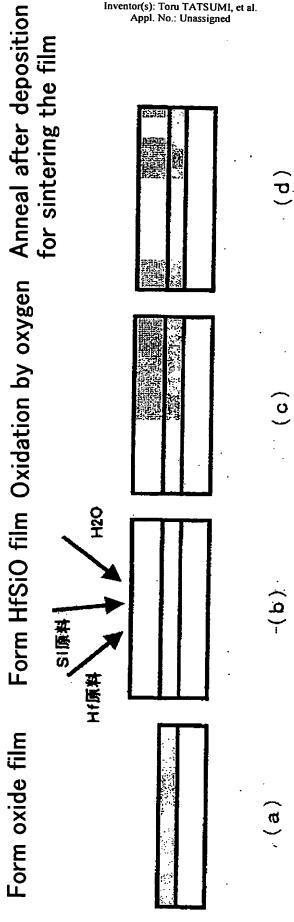
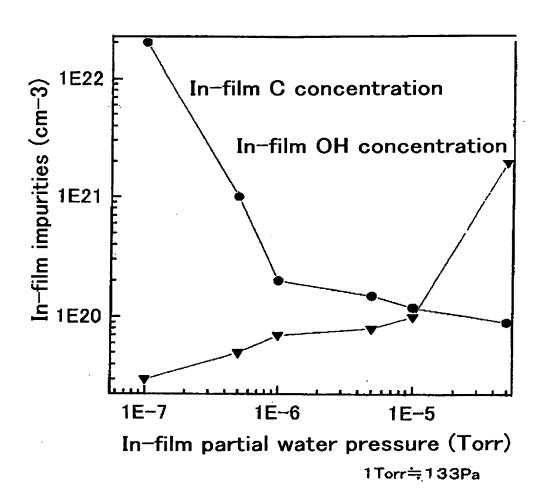


Fig. 10



Appl. No.: Unassigned

Fig. 11

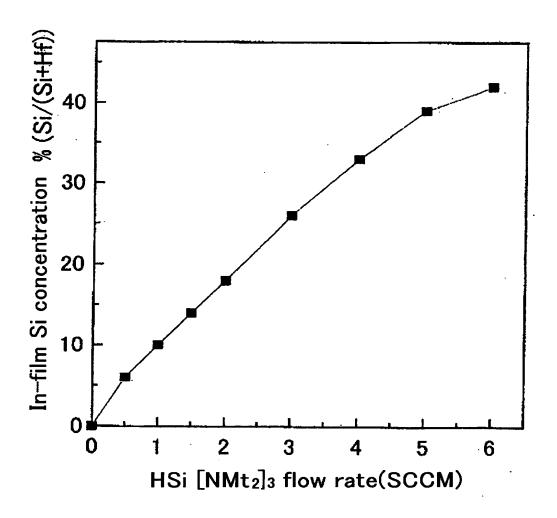


Fig. 12

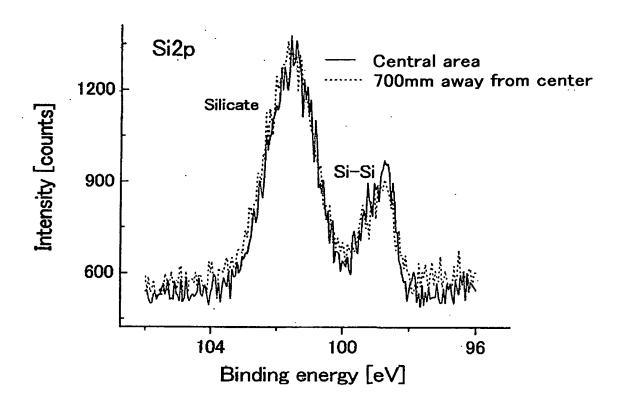


Fig. 13

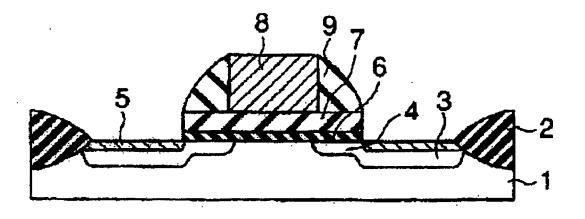


Fig. 14

